CPC COOPERATIVE PATENT CLASSIFICATION

H ELECTRICITY (NOTE omitted)

H03 ELECTRONIC CIRCUITRY

H03K PULSE TECHNIQUE (measuring pulse characteristics <u>G01R</u>; modulating sinusoidal oscillations with pulses <u>H03C</u>; transmission of digital information <u>H04L</u>; discriminator circuits detecting phase difference between two signals by counting or integrating cycles of oscillation <u>H03D 3/04</u>; automatic control, starting, synchronisation or stabilisation of generators of electronic oscillations or pulses where the type of generator is irrelevant or unspecified <u>H03L</u>; coding, decoding or code conversion, in general <u>H03M</u>)

NOTES

- 1. This subclass covers:
 - methods, circuits, devices or apparatus using active elements operating in a discontinuous or switching manner for generating, counting, amplifying, shaping, modulating, demodulating or otherwise manipulating signals;
 - electronic switching not involving contact-making and braking;
 - logic circuits handling electric pulses.
- 2. In this subclass, the following expression is used with the meaning indicated:
 - "active element" exercises control over the conversion of input energy into an oscillation or a discontinuous flow of energy.
- 3. In this subclass, where the claims of a patent document are not limited to a specific circuit element, the document is classified at least according to the elements used in the described embodiment.

WARNINGS

- 1. The following IPC groups are not in the CPC scheme. The subject matter for these IPC groups is classified in the following CPC groups:
- H03K 17/695
 covered by
 H03K 17/687

 2. In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.

3/00	Circuits for generating electric pulses; Monostable, bistable or multistable circuits (<u>H03K 4/00</u> takes precedence; for digital function generators in	3/023 by the use of differential amplifiers or comparators, with internal or external positive feedback
	computers <u>G06F 1/02</u>)	3/0231 Astable circuits {(<u>H03K 3/0315</u> takes
3/01	• Details	precedence)}
3/011	Modifications of generator to compensate for	3/02315 {Stabilisation of output, e.g. using crystal}
	variations in physical values, e.g. voltage,	3/0232 Monostable circuits
	temperature {(to maintain energy constant	3/0233 Bistable circuits
	<u>H03K 3/015</u>)}	3/02332 {of the master-slave type}
3/012	• Modifications of generator to improve response time or to decrease power consumption	3/02335 {provided with means for increasing reliability; for protection; for ensuring
3/013	• Modifications of generator to prevent operation by noise or interference	a predetermined initial state when the supply voltage has been applied; for storing
3/014	Modifications of generator to ensure starting of oscillations	the actual state when the supply voltage fails (digital storage cells each combining
3/015	• • Modifications of generator to maintain energy constant	volatile and non-volatile storage properties <u>G11C 14/00</u> }
3/017	 Adjustment of width or dutycycle of pulses (pulse width modulation <u>H03K 7/08</u> {; to maintain energy constant <u>H03K 3/015</u>}) 	3/02337 {Bistables with hysteresis, e.g. Schmitt trigger (non-regenerative amplitude discriminators <u>G01R 19/165</u>)}
3/02	. Generators characterised by the type of circuit	3/0234 Multistable circuits
	or by the means used for producing pulses (<u>H03K 3/64</u> - <u>H03K 3/84</u> take precedence)	3/027 by the use of logic circuits, with internal or external positive feedback
3/021	by the use, as active elements, of more than one	3/03 Astable circuits
	type of element or means, e.g. BIMOS, composite	3/0307 {Stabilisation of output, e.g. using crystal}
	devices such as IGBT	3/0315 {Ring oscillators}

3/0322	•••• {with differential cells}
3/033	Monostable circuits
3/037	Bistable circuits
3/0372	• • • • {of the master-slave type}
3/0375	• • • • {provided with means for increasing
	reliability; for protection; for ensuring
	a predetermined initial state when the
	supply voltage has been applied; for storing
	the actual state when the supply voltage
	fails (digital storage cells each combining volatile and non-volatile storage properties
	<u>G11C 14/00</u> }
3/0377	• • • {Bistables with hysteresis, e.g. Schmitt
5/05/1	trigger (non-regenerative amplitude
	discriminators <u>G01R 19/165</u>)}
3/038	Multistable circuits
3/04	• • by the use, as active elements, of vacuum tubes
5/01	only, with positive feedback ($H03K 3/023$,
	H03K 3/027 take precedence)
3/05	• • • using means other than a transformer for
	feedback
3/06	• • • • using at least two tubes so coupled that the
	input of one is derived from the output of
	another, e.g. multivibrator
3/08	• • • • • astable
3/09	Stabilisation of output
3/10	• • • • monostable
3/12	• • • • bistable
3/13	Bistables with hysteresis, e.g. Schmitt
	trigger
3/14	• • • • multistable
3/16	• • • using a transformer for feedback, e.g. blocking
	oscillator with saturable core
3/22	• • • • specially adapted for amplitude comparison,
2/26	i.e. Multiar
3/26	• by the use, as active elements, of bipolar transistors with internal or external positive
	feedback (<u>H03K 3/023, H03K 3/027</u> take
	precedence)
3/28	• • • using means other than a transformer for
	feedback
3/281	• • • • using at least two transistors so coupled that
	the input of one is derived from the output of
	another, e.g. multivibrator
3/282	• • • • • astable
3/2821	{Emitters connected to one another by
	using a capacitor}
3/2823	••••• {using two active transistor of the same
	conductivity type (<u>H03K 3/2821</u> takes
	precedence)}
3/2825	••••• {in an asymmetrical circuit
2/2026	configuration }
3/2826	\ldots \ldots {using two active transistors of the
	complementary type (<u>H03K 3/2821</u> take precedence)}
3/2828	
512020	•••••• {in an asymmetrical circuit configuration}
3/283	• • • • • • Stabilisation of output {, e.g. using
5,205	crystal}
3/284	• • • • • monostable
3/286	bistable
-	

3/2865	•	•	• • • • {ensuring a predetermined initial state
			when the supply voltage has been
			applied; storing the actual state when
			the supply voltage fails (digital storage cells each combining volatile and non-
			volatile storage properties <u>G11C 14/00</u>)
3/287			• • • using additional transistors in the
5/201	•	•	feedback circuit (<u>H03K 3/289</u> takes
			precedence)
3/288			using additional transistors in the input
			circuit (<u>H03K 3/289</u> takes precedence)
3/2885			••••• the input circuit having a differential
			configuration
3/289	•	•	of the master-slave type
3/2893	•	•	Bistables with hysteresis, e.g. Schmitt
			trigger
3/2897	•	•	••••• with an input circuit of differential
			configuration
3/29	•	•	multistable
3/30	•	•	• using a transformer for feedback, e.g. blocking
			oscillator
3/313	•	•	by the use, as active elements, of semiconductor
			devices with two electrodes, one or two potential barriers, and exhibiting a negative resistance
			characteristic
3/315			• the devices being tunnel diodes
3/33	•	•	by the use, as active elements, of semiconductor
5155	•	•	devices exhibiting hole storage or enhancement
			effect
3/335			by the use, as active elements, of semiconductor
			devices with more than two electrodes and
			exhibiting avalanche effect
3/35	•	•	by the use, as active elements, of bipolar
			semiconductor devices with more than two
			PN junctions, or more than three electrodes, or
			more than one electrode connected to the same
			conductivity region (<u>H03K 3/023</u> , <u>H03K 3/027</u> take precedence)
3/351			• the devices being unijunction transistors
5/551	•	•	(<u>H03K 3/352</u> takes precedence)
3/352			• the devices being thyristors
3/3525			Anode gate thyristors or programmable
	•	-	unijunction transistors
3/353			by the use, as active elements, of field-effect
			transistors with internal or external positive
			feedback (H03K 3/023, H03K 3/027 take
			precedence)
3/354	•	•	Astable circuits
3/3545	•	•	• • {Stabilisation of output, e.g. using crystal}
3/355	•	•	• Monostable circuits
3/356	•	•	• Bistable circuits
3/356008	•	•	• • {ensuring a predetermined initial state when
			the supply voltage has been applied; storing
			the actual state when the supply voltage fails (digital storage cells each combining
			volatile and non-volatile storage properties
			<u>G11C 14/00</u> }
3/356017			• • {using additional transistors in the input
	-	-	circuit (<u>H03K 3/356104</u> , <u>H03K 3/3562</u> take
			precedence)}
3/356026	•	•	• • • {with synchronous operation
			(<u>H03K 3/356034</u> , <u>H03K 3/356052</u> take
			precedence)}
3/356034	•	•	• • • {the input circuit having a differential
			configuration }

			• • • • {with synchronous operation}
			• • • {using pass gates}
			• • • { with synchronous operation }
3/356069			• • {using additional transistors in the feedback
			circuit (<u>H03K 3/356104</u> , <u>H03K 3/3562</u> take precedence)}
3/356078			
			 • { with additional means for controlling the
	•	•	main nodes (<u>H03K 3/356104</u> , <u>H03K 3/3562</u>
			take precedence)}
3/356095		•	• • • {with synchronous operation}
3/356104	•	•	• • {using complementary field-effect transistors
			(H03K 3/35625 takes precedence)}
3/356113	•	•	• • • {using additional transistors in the input circuit}
3/356121		•	• • • • {with synchronous operation
			(<u>H03K 3/35613</u> , <u>H03K 3/356147</u> take
			precedence)}
3/35613	•	•	•••• {the input circuit having a differential
2/25/120			configuration }
3/356139			••••• {with synchronous operation}
			• • • {using pass gates}
			••••• {with synchronous operation}
3/356165	•	•	• • • {using additional transistors in the feedback circuit}
3/356173			• • • {with synchronous operation}
			•••• {with additional means for controlling the
0,000102	•	•	main nodes}
3/356191			• • • { with synchronous operation }
3/3562			• • of the master-slave type
3/35625			• • • {using complementary field-effect
			transistors}
3/3565			• Bistables with hysteresis, e.g. Schmitt trigger
		-	• • Distudies with hysteresis, e.g. beninte trigger
3/3568	•	•	• Multistable circuits
3/3568 3/357	•	•	• Multistable circuits by the use, as active elements, of bulk negative
3/357		•	• Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices
		•	• Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors,
3/357 3/36		•	• Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for
3/357		•	• Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes,
3/357 3/36		•	• Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (<u>H03K 3/55</u> takes
3/357 3/36 3/37		•	• Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (<u>H03K 3/55</u> takes precedence)
3/357 3/36		•	• Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (<u>H03K 3/55</u> takes
3/357 3/36 3/37		•	 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (<u>H03K 3/55</u> takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical
3/357 3/36 3/37 3/38 3/40		•	 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (<u>H03K 3/55</u> takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells
3/357 3/36 3/37 3/38		•	 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic
3/357 3/36 3/37 3/38 3/40		•	 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric
3/357 3/36 3/37 3/38 3/40		•	 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric devices
3/357 3/36 3/37 3/38 3/40 3/42		•	 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric
3/357 3/36 3/37 3/38 3/40 3/42		•	 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled by the use, as active elements, of beam deflection tubes
3/357 3/36 3/37 3/38 3/40 3/42 3/43			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled by the use, as active elements, of beam deflection tubes
3/357 3/36 3/37 3/38 3/40 3/42 3/43			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices electrically- or optically-coupled by the use, as active elements, of beam deflection tubes by the use, as active elements, of non-linear
3/357 3/36 3/37 3/38 3/40 3/42 3/43 3/45			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (<u>H03K 3/55</u> takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled by the use, as active elements, of beam deflection tubes by the use, as active elements, of non-linear magnetic or dielectric devices
3/357 3/36 3/37 3/38 3/40 3/42 3/43 3/45 3/455			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled by the use, as active elements, of beam deflection tubes by the use, as active elements, of non-linear magnetic or dielectric devices {using thin films}
3/357 3/36 3/37 3/38 3/40 3/42 3/43 3/45 3/455 3/47			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled by the use, as active elements, of beam deflection tubes by the use, as active elements, of non-linear magnetic or dielectric devices {using thin films} the devices being parametrons the devices being ferro-resonant the devices being multi-aperture magnetic
3/357 3/36 3/37 3/38 3/40 3/42 3/43 3/45 3/455 3/47 3/49			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices electrically- or optically-coupled by the use, as active elements, of beam deflection tubes by the use, as active elements, of non-linear magnetic or dielectric devices {using thin films} the devices being parametrons the devices being multi-aperture magnetic cores, e.g. transfluxors
3/357 3/36 3/37 3/38 3/40 3/42 3/43 3/45 3/455 3/47 3/49			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices electrically- or optically-coupled by the use, as active elements, of beam deflection tubes by the use, as active elements, of non-linear magnetic or dielectric devices {using thin films} the devices being parametrons the devices being multi-aperture magnetic cores, e.g. transfluxors by the use of an energy-accumulating element
3/357 3/36 3/37 3/38 3/40 3/42 3/43 3/45 3/455 3/47 3/49 3/51			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices electrically- or optically-coupled by the use, as active elements, of beam deflection tubes by the use, as active elements, of non-linear magnetic or dielectric devices {using thin films} the devices being parametrons the devices being multi-aperture magnetic cores, e.g. transfluxors by the use of an energy-accumulating element discharged through the load by a switching
3/357 3/36 3/37 3/38 3/40 3/42 3/43 3/45 3/455 3/47 3/49 3/51			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled by the use, as active elements, of non-linear magnetic or dielectric devices { using thin films} the devices being parametrons the devices being multi-aperture magnetic cores, e.g. transfluxors by the use of an energy-accumulating element discharged through the load by a switching device controlled by an external signal and not
3/357 3/36 3/37 3/38 3/40 3/42 3/43 3/45 3/455 3/47 3/49 3/51			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled by the use, as active elements, of non-linear magnetic or dielectric devices {using thin films} the devices being parametrons the devices being multi-aperture magnetic cores, e.g. transfluxors by the use of an energy-accumulating element discharged through the load by a switching device controlled by an external signal and not incorporating positive feedback (H03K 3/335
3/357 3/36 3/37 3/38 3/40 3/42 3/43 3/45 3/455 3/47 3/49 3/51 3/53			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled by the use, as active elements, of non-linear magnetic or dielectric devices {using thin films} the devices being parametrons the devices being ferro-resonant the devices being multi-aperture magnetic cores, e.g. transfluxors by the use of an energy-accumulating element discharged through the load by a switching device controlled by an external signal and not incorporating positive feedback (H03K 3/335 takes precedence)
3/357 3/36 3/37 3/38 3/40 3/42 3/43 3/45 3/455 3/47 3/49 3/51			 Multistable circuits by the use, as active elements, of bulk negative resistance devices, e.g. Gunn-effect devices by the use, as active elements, of semiconductors, not otherwise provided for by the use, as active elements, of gas-filled tubes, e.g. astable trigger circuits (H03K 3/55 takes precedence) by the use, as active elements, of superconductive devices by the use, as active elements, of electrochemical cells by the use, as active elements, of opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled by the use, as active elements, of non-linear magnetic or dielectric devices {using thin films} the devices being parametrons the devices being multi-aperture magnetic cores, e.g. transfluxors by the use of an energy-accumulating element discharged through the load by a switching device controlled by an external signal and not incorporating positive feedback (H03K 3/335

3/55	• • the switching device being a gas-filled tube having a control electrode
3/57	• • • the switching device being a semiconductor
3/59	device • by the use of galvano-magnetic devices, e.g. Hall
5,57	effect devices
3/64	• Generators producing trains of pulses, i.e. finite sequences of pulses
3/66	• • by interrupting the output of a generator
3/70	•••• time intervals between all adjacent pulses of
	one train being equal
3/72	• • with means for varying repetition rate of trains
3/78	• Generating a single train of pulses having a predetermined pattern, e.g. a predetermined number
3/80	• Generating trains of sinusoidal oscillations (by
5/00	keying or interruption of sinusoidal oscillations <u>H03C</u> ; for transmission of digital information H04L)
3/84	• Generating pulses having a predetermined statistical distribution of a parameter, e.g. random pulse
	generators
3/86	• Generating pulses by means of delay lines and not covered by the preceding subgroups
4/00	Generating pulses having essentially a finite slope
	or stepped portions
4/02	• having stepped portions, e.g. staircase waveform
4/023	• • {by repetitive charge or discharge of a capacitor,
	analogue generators}
4/026	• • {using digital techniques}
4/04	 having parabolic shape
4/06	• having triangular shape
4/063	• {high voltage - or current generators}
4/066	 {using a Miller-integrator (<u>H03K 4/08</u> takes precedence)}
4/08	 having sawtooth shape
4/085	 {Protection of sawtooth generators}
4/10	 using as active elements vacuum tubes only
4/12	in which a sawtooth voltage is produced
1/12	across a capacitor
4/14	using two tubes so coupled that the input
	of each one is derived from the output of
	the other, e.g. multivibrator
4/16	••••• using a single tube with positive feedback through transformer, e.g. blocking oscillator
4/18	using a single tube exhibiting negative
	resistance between two of its electrodes,
	e.g. transitron, dynatron
4/20	using a tube with negative feedback by
	capacitor, e.g. Miller integrator
4/22	••••• combined with transitron, e.g.
4/24	phantastron, sanatron
4/24	 Boot-strap generators in which a sawtooth current is produced
4/20	through an inductor
4/28	• • • • using a tube operating as a switching
	device
4/32	••••• combined with means for generating the driving pulses
4/34	•••••• using a single tube with positive
	feedback through a transformer

4/36	••••••••••••••••••••••••••••••••••••••
4/38	••••• combined with Miller integrator
4/39	••••• using a tube operating as an amplifier
4/41	••••••••••••••••••••••••••••••••••••••
4/43	••••• combined with means for generating the driving pulses
4/48	• • using as active elements semiconductor devices (<u>H03K 4/787</u> - <u>H03K 4/84</u> take precedence)
4/50	• • • in which a sawtooth voltage is produced across a capacitor
4/501	••••• the starting point of the flyback period being determined by the amplitude of the voltage across the capacitor, e.g. by a comparator
4/502	the capacitor being charged from a constant-current source
4/52	• • • • using two semiconductor devices so
	coupled that the input of each one is derived from the output of the other, e.g. multivibrator
4/54	• • • • using a single semiconductor device with
101	positive feedback through a transformer, e.g. blocking oscillator
4/56	using a semiconductor device with
	negative feedback through a capacitor, e.g. Miller integrator
4/58	Boot-strap generators
4/60	in which a sawtooth current is produced
	through an inductor
4/62	••••• using a semiconductor device operating as a switching device
4/625	••••••••••••••••••••••••••••••••••••••
	e.g. class D, switched mode}
4/64	••••• combined with means for generating the driving pulses {(<u>H03K 4/625</u> takes precedence)}
4/66	••••••••••••••••••••••••••••••••••••••
4/68	• • • • • • • Generators in which the switching
	device is conducting during the fly-back part of the cycle
4/69	using a semiconductor device operating as an amplifier
4/693	••••• {operating in push-pull, e.g. class B (<u>H03K 4/696</u> takes precedence)}
4/696	{using means for reducing power dissipation or for shortening the flyback
	time, e.g. applying a higher voltage
	during flyback time}
4/71	• • • • • with negative feedback through a
4/72	 capacitor, e.g. Miller-integrator combined with means for generating the driving pulses
4/725	
	• • • • • • {Push-pull amplifier circuits}
4/787	• • using as active elements semiconductor devices with two electrodes and exhibiting a negative
	resistance characteristic
4/793	
4/793 4/80	 using tunnel diodes using as active elements multi-layer diodes
4/ OU	•••• using as active elements multi-laver diodes

4/83	• • • using as active elements semiconductor devices with more than two PN junctions or with more than three electrodes or more than one
	electrode connected to the same conductivity region
4/835	• • • {using pulse-modulation techniques for the
	generation of the sawtooth wave, e.g. class D, switched mode}
4/84	Generators in which the semiconductor
.,	device is conducting during the fly-back
	part of the cycle {(<u>H03K 4/835</u> takes precedence)}
4/86	• • • using as active elements gas-filled tubes {or
1/22	spark-gaps}
4/88	 using as active elements electrochemical cells {or galvano-magnetic or photo-electric elements}
4/90	Linearisation of ramp (modifying slopes
	of pulses H03K 6/04; scanning distortion
	correction for television receivers <u>H04N 3/23</u>); Synchronisation of pulses
4/92	• having a waveform comprising a portion of a
	sinusoid (generating sinusoidal oscillations H03B)
4/94	• having trapezoidal shape
5/00	Manipulating of pulses not covered by one of the other main groups of this subclass (circuits
	with regenerative action <u>H03K 3/00</u> , <u>H03K 4/00</u> ; by
	the use of non-linear magnetic or dielectric devices
	<u>H03K 3/45</u>)
	<u>NOTE</u>
	In this group, the input signals are of the pulse type.
5/00006	• {Changing the frequency (modulating
	pulses <u>H03K 7/00;</u> frequency dividers <u>H03K 21/00</u> - <u>H03K 29/00;</u> additive or subtractive
	mixing of two pulse rates into one <u>G06F 7/605;</u>
	pulse rate dividers <u>G06F 7/68</u>)}
2005/00013	• {Delay, i.e. output pulse is delayed after input pulse and pulse length of output pulse is dependent on
	pulse length of input pulse}
2005/00019	• • {Variable delay}
2005/00026	
2005/00032	obtained after conversion by a D/A converter} {Dc control of switching transistors}
2005/00039	• • • • {having four transistors serially}
2005/00045	• • • • {Dc voltage control of a capacitor or of the
2005/00052	coupling of a capacitor as a load}fy mixing the outputs of fixed delayed
2005/00052	•••• {by mixing the outputs of fixed delayed signals with each other or with the input signal}
2005/00058	
2005/00065	• • • {by current control, e.g. by parallel current control transistors}
2005/00071	• • • • {by adding capacitance as a load}
2005/00078	
2005/00084	
2005/00091 2005/00097	 {using fuse links} {Avoiding variations of delay using feedback,
2000/000/1	e.g. controlled by a PLL}
2005/00104	• • • {using a reference signal, e.g. a reference
	clock}

2005/0011	• • • • {using a separate time interval to calibrate the delay}
2005/00117	• • {Avoiding variations of delay due to line termination}
2005/00123	• • {Avoiding variations of delay due to integration tolerances}
2005/0013	• • {Avoiding variations of delay due to power supply}
2005/00136	• • {Avoiding asymmetry of delay for leading or trailing edge; Avoiding variations of delay due to threshold}
2005/00143	• • {Avoiding variations of delay due to temperature}
2005/0015	• • {Layout of the delay element}
2005/00156	• • {using opamps, comparators, voltage multipliers or other analog building blocks}
2005/00163	
2005/00169	
2005/00176	• • • {using differential stages}
2005/00170	••••• {using constant current sources}
2005/00182	
2005/00195	
2005/00202	{using current mirrors}
2005/00208	(
2005/00215	
	FET's is in parallel or in series, all having the
2005/00221	same gate control}
2005/00221	• • • { where the conduction path of the different output FET's is connected in parallel with
	different gate control, e.g. having different
	sizes or thresholds, or coupled through
	different resistors}
2005/00228	A starting complementary input and output
2003/00220	signals}
2005/00234	• • {using circuits having two logic levels}
2005/00234	
2005/00247	• • • {using counters}
2005/00247	••••• {using microprocessors}
2005/00254	{using menories or FIFO's}
2005/00267	· · · · · · · · · · · · · · · · · · ·
2005/00287	 {using D/A or A/D converters} {using digital comparators}
2005/0028	• • {using varicaps, e.g. gate capacity of a FET with specially defined threshold, as delaying
	capacitors}
2005/00286	
2005/00280	input pulse is dependent on the frequency, and such
	that a phase difference is obtained independent of
	the frequency }
2005/00293	
	or a falling edge, the length of the output pulse
	not being in relation with the length of the input
	triggering pulse}
5/003	. Changing the DC level (reinsertion of dc component
	of a television signal H04N 5/16)
5/007	• Base line stabilisation (thresholding H03K 5/08)
5/01	• Shaping pulses (discrimination against noise or
	interference $H03K 5/125$)
5/02	• • by amplifying (<u>H03K 5/04</u> takes precedence)
5/023	• • {using field effect transistors}
5/026	• • • {with a bidirectional operation}
5/04	• by increasing duration; by decreasing duration
5/05	 by mercasing duration, by decreasing duration by the use of clock signals or other time
2,05	reference signals
	G

5/06	• • • by the use of delay lines or other analogue
	delay elements
5/065	• • • {using dispersive delay lines}
5/07	• • by the use of resonant circuits
5/08	• by limiting; by thresholding; by slicing, i.e.
	combined limiting and thresholding (H03K 5/07 takes precedence; comparing one pulse with
	another <u>H03K 5/22</u> ; providing a determined
	threshold for switching H03K 17/30)
5/082	• • { with an adaptive threshold }
5/084	•••• {modified by switching, e.g. by a periodic
	signal or by a signal in synchronism with the
	transitions of the output signal}
5/086	• • • {generated by feedback}
5/088	•••• {modified by switching, e.g. by a periodic
	signal or by a signal in synchronism with
	the transitions of the output signal}
5/12	• • by steepening leading or trailing edges
5/125	• Discriminating pulses (measuring characteristics
	of individual pulses <u>G01R 29/02</u> ; separation
	of synchronising signals in television systems H04N 5/08)
5/1252	Suppression or limitation of noise or interference
5/1252	(specially adapted for transmission systems
	H04B 15/00, H04L 25/08)
5/1254	• • • specially adapted for pulses generated by
	closure of switches, i.e. anti-bouncing devices
	(debouncing circuits for electronic time-pieces
	<u>G04G 5/00</u>)
5/13	• Arrangements having a single output and
	transforming input signals into pulses delivered at desired time intervals
5/131	Digitally controlled
5/131	 using a chain of active delay devices
5/134	• • with field-effect transistors
5/135	• by the use of time reference signals, e.g. clock
	signals
5/14	• • by the use of delay lines ($\underline{H03K 5/133}$ takes
	precedence)
5/145	• • by the use of resonant circuits
5/15	• Arrangements in which pulses are delivered
	at different times at several outputs, i.e. pulse distributors (distributing, switching or gating
	arrangements H03K 17/00)
5/15006	• {with two programmable outputs}
5/15013	• {with more than two outputs}
5/1502	• • {programmable}
5/15026	• • {with asynchronously driven series connected
	output stages}
5/15033	• • • { using a chain of bistable devices }
5/1504	• • • { using a chain of active delay devices
	(H03K 5/15053 takes precedence)}
5/15046	• • • { using a tapped delay line }
5/15053	
	• • • {using a chain of monostable devices}
5/1506	 {using a chain of monostable devices} {with parallel driven output stages; with
5/1506	 {using a chain of monostable devices} {with parallel driven output stages; with synchronously driven series connected output
	 {using a chain of monostable devices} {with parallel driven output stages; with synchronously driven series connected output stages}
5/15066	 {using a chain of monostable devices} . {with parallel driven output stages; with synchronously driven series connected output stages} {using bistable devices (H03K 5/15093 takes
5/15066	 . {using a chain of monostable devices} . {with parallel driven output stages; with synchronously driven series connected output stages} . {using bistable devices (<u>H03K 5/15093</u> takes precedence)}
5/15066 5/15073	 {using a chain of monostable devices} . {with parallel driven output stages; with synchronously driven series connected output stages} {using bistable devices (<u>H03K 5/15093</u> takes precedence)} {using a plurality of comparators}
5/15066	 {using a chain of monostable devices} . {with parallel driven output stages; with synchronously driven series connected output stages} {using bistable devices (H03K 5/15093 takes precedence)} {using a plurality of comparators} {using a plurality of delay lines}
5/15066 5/15073 5/1508	 {using a chain of monostable devices} {with parallel driven output stages; with synchronously driven series connected output stages} {using bistable devices (H03K 5/15093 takes precedence)} {using a plurality of comparators} {using a plurality of delay lines} {using a plurality of monostables devices}
5/15066 5/15073 5/1508 5/15086	 {using a chain of monostable devices} {with parallel driven output stages; with synchronously driven series connected output stages} {using bistable devices (H03K 5/15093 takes precedence)} {using a plurality of comparators} {using a plurality of delay lines} {using a plurality of monostables devices}

5/1515 5/153	 {non-overlapping} Arrangements in which a pulse is delivered at the instant when a predetermined characteristic of an input signal is present or at a fixed time interval after this instant (switching at zero crossing
5/1532	<u>H03K 17/13</u>) • Peak detectors (measuring characteristics of
5/1552	individual pulses <u>G01R 29/02</u>)
5/1534	Transition or edge detectors
5/1536	• Zero-crossing detectors (in measuring circuits <u>G01R 19/175</u>)
5/156	• Arrangements in which a continuous pulse train is transformed into a train having a desired pattern
5/1565	• {the output pulses having a constant duty cycle}
5/159	• Applications of delay lines not covered by the preceding subgroups
5/19	 Monitoring patterns of pulse trains (indicating amplitude <u>G01R 19/00</u>; indicating frequency
	G01R 23/00; measuring characteristics of individual
5/22	pulses <u>G01R 29/02</u>)
5/22	• Circuits having more than one input and one output for comparing pulses or pulse trains with each other
	according to input signal characteristics, e.g. slope,
	integral (indicating phase difference of two cyclic
5/04	pulse trains <u>G01R 25/00</u>)
5/24 5/2409	 the characteristic being amplitude {using bipolar transistors (<u>H03K 5/2436</u> takes
5/2409	precedence)}
5/2418	• • • {with at least one differential stage}
5/2427	•••• {using clock signals}
5/2436	• • • {using a combination of bipolar and field-effect transistors}
5/2445	• • • { with at least one differential stage }
5/2454	• • • • {using clock signals}
5/2463 5/2472	 . {using diodes} . {using field effect transistors (<u>H03K 5/2436</u>
	takes precedence)}
5/2481 5/249	 {with at least one differential stage} {using clock signals}
5/249	 the characteristic being duration, interval,
5/20	position, frequency, or sequence
6/00	Manipulating pulses having a finite slope and
	not covered by one of the other main groups
	of this subclass (circuits with regenerative action H03K 4/00)
6/02	• Amplifying pulses
6/04	• Modifying slopes of pulses, e.g. S-correction (S-
	correction in television H04N 3/23)
7/00	Modulating pulses with a continuously-variable modulating signal
7/02	• Amplitude modulation, i.e. PAM
7/04	• Position modulation, i.e. PPM
7/06	• Frequency or rate modulation, i.e. PFM or PRM
7/08	 Duration or width modulation {; Duty cycle modulation}
7/10	• Combined modulation, e.g. rate modulation and amplitude modulation
9/00	Demodulating pulses which have been modulated with a continuously-variable signal
9/02	• of amplitude-modulated pulses
9/04	• of position-modulated pulses
9/06	• of frequency- or rate-modulated pulses

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- 9/08 . of duration- or width-mudulated pulses {or of dutycycle modulated pulses }
- 9/10 of pulses having combined modulation
- 11/00 Transforming types of modulations, e.g. positionmodulated pulses into duration-modulated pulses
- 12/00 Producing pulses by distorting or combining sinusoidal waveforms (shaping pulses <u>H03K 5/01</u>; combining sinewaves using elements operating in a non-switching manner <u>H03B 21/00</u>)
 17/00 Electronic switching or gating, i.e. not by contact-
- making and -breaking (gated amplifiers H03F 3/72; switching arrangements for exchange systems using static devices H04Q 3/52) 17/002 • {Switching arrangements with several input- or output terminals (code converters H03M 5/00, H03M 7/00)} 17/005 • • {with several inputs only} 17/007 • { with several outputs only } 17/04 . Modifications for accelerating switching 17/0403 • {in thyristor switches} 17/0406 • {in composite switches} 17/041 . . without feedback from the output circuit to the control circuit {(H03K 17/0403, H03K 17/0406 take precedence) 17/04106 . . . {in field-effect transistor switches (H03K 17/0412, H03K 17/0416 take precedence)} 17/04113 . . . {in bipolar transistor switches (H03K 17/0412, H03K 17/0416 take precedence) 17/0412 . . . by measures taken in the control circuit 17/04123 . . . {in field-effect transistor switches} 17/04126 . . . {in bipolar transistor switches} 17/0414 . . . Anti-saturation measures 17/0416 . . . by measures taken in the output circuit 17/04163 . . . {in field-effect transistor switches} 17/04166 {in bipolar transistor switches} 17/042 . . by feedback from the output circuit to the control circuit {(<u>H03K 17/0403</u>, <u>H03K 17/0406</u> take precedence)} 17/04206 . . . {in field-effect transistor switches} 17/04213 . . . {in bipolar transistor switches} 17/0422 . . . Anti-saturation measures 17/0424 . . . by the use of a transformer 17/06 . Modifications for ensuring a fully conducting state • • {in field-effect transistor switches} 17/063 2017/066 • • {Maximizing the OFF-resistance instead of minimizing the ON-resistance} 17/08 . Modifications for protecting switching circuit against overcurrent or overvoltage 2017/0803 . . {against radiation hardening} 2017/0806 • • {against excessive temperature} 17/081 . . without feedback from the output circuit to the control circuit 17/08104 . . . {in field-effect transistor switches (H03K 17/0812, H03K 17/0814 take precedence)} 17/08108 . . . { in thyristor switches (H03K 17/0812, H03K 17/0814 take precedence) 17/08112 . . . {in bipolar transistor switches (H03K 17/0812, H03K 17/0814 take precedence) 17/08116 . . . {in composite switches (<u>H03K 17/0</u>812, H03K 17/0814 take precedence)

17/0812	by measures taken in the control circuit
17/08122	• • • { in field-effect transistor switches }
17/08124	• • • {in thyristor switches}
17/08126	
17/08128	• • • {in composite switches}
17/0814	• • • by measures taken in the output circuit
17/08142	• • • {in field-effect transistor switches}
17/08144	• • • {in thyristor switches}
17/08146	• • • {in bipolar transistor switches}
17/08148	• • • {in composite switches}
17/082	• • by feedback from the output to the control circuit
17/0822	• • {in field-effect transistor switches}
17/0824	• • { in thyristor switches }
17/0826	• • {in bipolar transistor switches}
17/0828	• • {in composite switches}
17/10	. Modifications for increasing the maximum
	permissible switched voltage
17/102	• {in field-effect transistor switches}
17/105	• • {in thyristor switches}
17/107	• • {in composite switches}
17/12	• Modifications for increasing the maximum
	permissible switched current
17/122	• {in field-effect transistor switches}
17/125	• • {in thyristor switches}
17/127	• • {in composite switches}
17/13	Modifications for switching at zero crossing
	(generating an impulse at zero crossing
	<u>H03K 5/1536</u>)
17/133	• • {in field-effect transistor switches}
17/136	• • {in thyristor switches}
17/14	• Modifications for compensating variations of
	physical values, e.g. of temperature
17/145	• {in field-effect transistor switches}
17/16	• Modifications for eliminating interference voltages
	or currents
17/161	• {in field-effect transistor switches}
17/162	• • • {without feedback from the output circuit to the
17/1/2	control circuit }
17/163	• • • {Soft switching}
17/164	• • • • {using parallel switching arrangements}
17/165	• • • {by feedback from the output circuit to the
17/166	<pre>control circuit } {Soft switching}</pre>
17/167	• • • • {using parallel switching arrangements}
17/168	• {in composite switches}
17/18	• Modifications for indicating state of switch
17/20	• Modifications for resetting core switching units to a predetermined state
17/22	predetermined state
1//22	Modifications for ansuring a predatermined initial
	• Modifications for ensuring a predetermined initial state when the surply voltage has been applied (hi-
	state when the supply voltage has been applied (bi-
17/223	state when the supply voltage has been applied (bi- stable generators $HO3K 3/12$)
17/223	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) . {in field-effect transistor switches}
2017/226	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) . {in field-effect transistor switches} . {in bipolar transistor switches}
	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) . {in field-effect transistor switches} . {in bipolar transistor switches} . Storing the actual state when the supply voltage
2017/226 17/24	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) (in field-effect transistor switches) {in bipolar transistor switches} Storing the actual state when the supply voltage fails
2017/226	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) . {in field-effect transistor switches} . {in bipolar transistor switches} . Storing the actual state when the supply voltage fails . Modifications for temporary blocking after receipt
2017/226 17/24	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) {in field-effect transistor switches} {in bipolar transistor switches} Storing the actual state when the supply voltage fails Modifications for temporary blocking after receipt of control pulses
2017/226 17/24 17/26	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) {in field-effect transistor switches} {in bipolar transistor switches} Storing the actual state when the supply voltage fails Modifications for temporary blocking after receipt of control pulses Modifications for introducing a time delay before
2017/226 17/24 17/26	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) {in field-effect transistor switches} {in bipolar transistor switches} Storing the actual state when the supply voltage fails Modifications for temporary blocking after receipt of control pulses
2017/226 17/24 17/26	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) . {in field-effect transistor switches} . {in bipolar transistor switches} . Storing the actual state when the supply voltage fails Modifications for temporary blocking after receipt of control pulses Modifications for introducing a time delay before switching (modifications to provide a choice
2017/226 17/24 17/26	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) . {in field-effect transistor switches} . {in bipolar transistor switches} . Storing the actual state when the supply voltage fails Modifications for temporary blocking after receipt of control pulses Modifications for introducing a time delay before switching (modifications to provide a choice of time-intervals for executing more than one
2017/226 17/24 17/26 17/28	 state when the supply voltage has been applied (bi- stable generators <u>H03K 3/12</u>) {in field-effect transistor switches} {in bipolar transistor switches} Storing the actual state when the supply voltage fails Modifications for temporary blocking after receipt of control pulses Modifications for introducing a time delay before switching (modifications to provide a choice of time-intervals for executing more than one switching action <u>H03K 17/296</u>)

17/292	 in thyristor, unijunction transistor or programmable unijunction transistor switches
17/296	• Time-programme switches providing a choice of time-intervals for executing more than one
	switching action and automatically terminating
	their operation after the programme is completed
	(electronic clocks comprising means to be operated
	at preselected times or after preselected time-
17/20	intervals <u>G04G 15/00</u>) Modifications for providing a productormined
17/30	• Modifications for providing a predetermined threshold before switching (shaping pulses by
	thresholding H03K 5/08)
17/302	• {in field-effect transistor switches}
17/305	• {in thyristor switches}
2017/307	• • {circuits simulating a diode, e.g. threshold zero}
17/51	characterised by the components used
	(<u>H03K 17/04</u> - <u>H03K 17/30</u> , <u>H03K 17/94</u> take
2017/515	precedence). {Mechanical switches; Electronic switches
2017/313	controlling mechanical switches, e.g. relais}
17/52	• • by the use, as active elements, of gas-filled tubes
17/54	• • by the use, as active elements of vacuum tubes
	(using diodes <u>H03K 17/74</u>)
17/545	• • • {using microengineered devices, e.g. field
17/56	emission devices}
17/56	• by the use, as active elements, of semiconductor devices (using diodes <u>H03K 17/74</u>)
17/567	• • Circuits characterised by the use of more than
	one type of semiconductor device, e.g. BIMOS,
	composite devices such as IGBT
17/58	• • • the devices being tunnel diodes
17/60	• • • the devices being bipolar transistors (bipolar
	transistors having four or more electrodes H03K 17/72)
17/601	• • • { using transformer coupling (H03K 17/61
	takes precedence)}
17/602	• • • {in integrated circuits}
17/603	•••• {with coupled emitters}
17/605	• • • • with galvanic isolation between the control circuit and the output circuit (H03K 17/78
	takes precedence)
17/61	• • • • using transformer coupling
17/615	• • • in a Darlington configuration
17/62	Switching arrangements with several
	input- output-terminals, e.g. multiplexers,
	distributors (logic circuits <u>H03K 19/00;</u> code converters <u>H03M 5/00, H03M 7/00</u>)
17/6207	• • • • • { without selecting means
17/0207	(<u>H03K 17/6242</u> - <u>H03K 17/6285</u> take
	precedence)}
17/6214	• • • • • {using current steering means}
17/6221	• • • • {combined with selecting means
	(<u>H03K 17/6242</u> - <u>H03K 17/6285</u> take precedence)}
17/6228	• • • • • {using current steering means}
17/6235	• • • • • {with storage of control signal}
17/6242	{with several inputs only and without
	selecting means}
17/625	• • • • • {using current steering means}
17/6257	• • • • {with several inputs only combined with selecting means}
17/6264	• • • • • {using current steering means}
17/6271	••••••••••••••••••••••••••••••••••••••
	selecting means}

17/6278	••••• {using current steering means}
17/6285	••••••••••••••••••••••••••••••••••••••
17/0205	selecting means}
17/6292	• • • • • {using current steering means}
17/64	• • • • having inductive loads
17/66	••••••••••••••••••••••••••••••••••••••
1//00	current in either direction at will; Switching arrangements for reversing the current at will
17/661	• • • • {connected to both load terminals}
17/662	••••• {each output circuit comprising more than one controlled bipolar transistor}
17/663	••••• {using complementary bipolar transistors}
17/664	••••• {in a symmetrical configuration}
17/665	• • • • {connected to one load terminal only}
17/666	••••• { the output circuit comprising more than one controlled bipolar transistor }
17/667	••••• {using complementary bipolar
	transistors}
17/668	••••• {in a symmetrical configuration}
17/68	specially adapted for switching ac currents or
	voltages
17/687	the devices being field-effect transistors
17/6871	{the output circuit comprising more than one controlled field-effect transistor}
17/6872	• • • • {using complementary field-effect transistors}
17/6874	•••• {in a symmetrical configuration}
2017/6875	•••• {using self-conductive, depletion FETs}
17/6877	{the control circuit comprising active
	elements different from those used in the
	output circuit}
2017/6878	• • • {using multi-gate field-effect transistors}
17/689	• • • with galvanic isolation between the control circuit and the output circuit (<u>H03K 17/78</u>
	takes precedence)
17/6895	• • • • {using acoustic means}
17/691	• • • • • using transformer coupling
17/693	Switching arrangements with several input-
	or output-terminals, e.g. multiplexers, distributors (logic circuits <u>H03K 19/00</u> ; code
	converters <u>H03M 5/00</u> , <u>H03M 7/00</u>)
17/70	• • the devices having only two electrodes and
	exhibiting negative resistance (the devices being tunnel diodes <u>H03K 17/58</u>)
17/72	A sing more than two PN junctions; having
1///2	more than three electrodes; having more
	than one electrode connected to the same
	conductivity region
17/722	with galvanic isolation between the control
	circuit and the output circuit (H03K 17/78
	takes precedence)
17/7225	• • • • {using acoustic means}
17/723	using transformer coupling
17/725	for ac voltages or currents (<u>H03K 17/722</u> , <u>H03K 17/735</u> take precedence)
17/73	• • • • for dc voltages or currents (<u>H03K 17/722</u> ,
1///5	<u>H03K 17/735</u> take precedence)
17/731	•••• {with inductive load}
17/732	Measures for enabling turn-off

17/735	•••• Switching arrangements with several input- or output-terminals, e.g. multiplexers, distributors (<u>H03K 17/722</u> takes precedence; logic circuits <u>H03K 19/00</u> ; code converters
	<u>H03M 5/00, H03M 7/00</u>)
17/74	 by the use, as active elements, of diodes (by the use of more than one type of semiconductor device <u>H03K 17/567</u>; by the use of tunnel diodes <u>H03K 17/58</u>; by the use of negative resistance diodes <u>H03K 17/70</u>)
17/76	Switching arrangements with several input- or output-terminals, e.g. multiplexers, distributors (logic circuits <u>H03K 19/00</u> ; code converters <u>H03M 5/00</u> , <u>H03M 7/00</u>)
17/78	using opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled
17/785	controlling field-effect transistor switches
17/79	• • • controlling {bipolar} semiconductor switches with more than two PN-junctions, or more than three electrodes, or more than one electrode connected to the same conductivity region
17/795	controlling bipolar transistors
17/7955	• • • {using phototransistors}
17/80	 using non-linear magnetic devices; using non-linear dielectric devices {(<u>H03K 17/95</u>, <u>H03K 17/97</u> take precedence)}
17/81	Switching arrangements with several input- or output-terminals, e.g. multiplexers, distributors (logic circuits <u>H03K 19/00</u> ; code converters <u>H03M 5/00</u> , H03M 7/00)
17/82	• • • the devices being transfluxors
17/84	 the devices being thansholds the devices being thin-film devices
17/86	 the devices being thin find devices the devices being twistors
17/88	• By the use, as active elements, of beam-deflection
17/00	tubes
17/90	 by the use, as active elements, of galvano- magnetic devices, e.g. Hall-effect devices (<u>H03K 17/95</u>, <u>H03K 17/97</u> take precedence)
17/92	• • by the use, as active elements, of superconductive devices
17/94	• characterised by the way in which the control signals are generated
17/941	 {using an optical detector (<u>H03K 17/968</u> takes precedence)}
17/943	• • • {using a plurality of optical emitters or detectors, e.g. keyboard}
17/945	• Proximity switches (<u>H03K 17/96</u> takes precedence)
2017/9455	• • • {constructional details (of proximity switches using a magnetic detector <u>H03K 17/9505</u>)}
17/95	• • • using a magnetic detector
17/9502	• • • • {Measures for increasing reliability}
17/9505	{Constructional details}
2017/9507	• • • • • {with illumination}
17/951	• • • • {Measures for supplying operating voltage to the detector circuit}
17/9512	• • • • {using digital techniques}
17/9515	• • • { using non-linear magnetic devices }
17/9517	• • • {using galvanomagnetic devices}
17/952	• • • • {using inductive coils}
17/9522	•••• {with a galvanically isolated probe}
17/9525	{controlled by an oscillatory signal (H03K 17/9537 takes precedence)}

2017/9527	• • • • {Details of coils in the emitter or receiver;
	Magnetic detector comprising emitting and
17/953	receiving coils}
17/935	{forming part of an oscillator (<u>H03K 17/9537</u> takes precedence)}
17/9532	• • • • • {with variable frequency}
17/9535	{with variable inequency}
17/9535	{in a resonant circuit}
17/9537	{controlled by an oscillatory signal}
17/9542	{forming part of an oscillator}
17/9545	{with variable frequency}
17/9545	{with variable inequency}
17/9547	 using a capacitive detector
17/96	Touch switches (specially adapted for electronic
17/90	time-pieces with no moving parts <u>G04G 21/08</u>)
2017/9602	 . {characterised by the type or shape of the
2017/9002	sensing electrodes}
2017/9604	• • • {characterised by the number of electrodes}
2017/9606	• • • • {using one electrode only per touch
201779000	switch}
2017/9609	••••• {where the electrode is the object to be
	switched}
2017/9611	••••• {where the electrode is a plant}
2017/9613	•••• {using two electrodes per touch switch}
2017/9615	•••• {using three electrodes per touch switch}
17/9618	• • { using a plurality of detectors, e.g. keyboard }
17/962	• • {Capacitive touch switches}
17/9622	• • • { using a plurality of detectors, e.g.
	keyboard}
17/9625	• • • {using a force resistance transducer}
17/9627	• • • {Optical touch switches}
17/9629	•••• {using a plurality of detectors, e.g.
	keyboard}
17/9631	• • • { using a light source as part of the switch }
2017/9634	•••• {using organic light emitting devices, e.g.
	light emitting polymer [OEP] or OLED}
17/9636	• • • • {using a pulsed light source}
17/9638	• • • { using a light guide }
17/964	• • • {Piezoelectric touch switches}
17/9643	• • • {using a plurality of detectors, e.g.
	keyboard}
17/9645	• • • {Resistive touch switches}
17/9647	• • • • {using a plurality of detectors, e.g.
17/0/5	keyboard}
17/965	• Switches controlled by moving an element forming part of the switch
17/967	forming part of the switch ••• having a plurality of control members, e.g.
17/907	keyboard (H03K 17/969, H03K 17/972,
	HO3K 17/909, HO3K 17/972, HO3K 17/98 take precedence)
17/968	using opto-electronic devices
17/969	 having a plurality of control members, e.g.
1.1.2.02	keyboard
17/97	• • • using a magnetic movable element
2017/9706	{Inductive element}
2017/9713	• • • • {Multiposition, e.g. involving comparison
	with different thresholds}
17/972	•••• having a plurality of control members, e.g.
	keyboard
17/975	• • • using a capacitive movable element
2017/9755	• • • • {Ohmic switch;}
17/98	having a plurality of control members, e.g.
	keyboard

19/00	Logic circuits, i.e. having at least two inputs acting					
	n one output (circuits for computer systems using					
	fuzzy logic G06N 7/02); Inverting circuits					
19/0002	• {Multistate logic (<u>H03K 19/02</u> takes precedence)}					
19/0005	• {Modifications of input or output impedance}					
19/0008 19/001	 {Arrangements for reducing power consumption} {in bipolar transistor circuits} 					
19/001	 {In opoint transistor circuits} {in field effect transistor circuits} 					
19/0015	 {In field effect transistor circuits} {by using a control or a clock signal, e.g. in order 					
17/0010	to apply power supply}					
19/0019	• {by energy recovery or adiabatic operation}					
19/0021	• {Modifications of threshold (for electronic					
	switching or gating H03K 17/30)}					
19/0024	• • {in bipolar transistor circuits}					
19/0027	• • {in field effect transistor circuits}					
19/003	• Modifications for increasing the reliability {for					
19/00307	protection }					
19/00307	 . {in bipolar transistor circuits} . {in field-effect transistor circuits} 					
19/00313	 {In held-effect transition effectives} {Delay compensation} 					
19/00323	 {Radiation hardening} 					
19/00338	• • {In field effect transistor circuits}					
19/00346	• • {Modifications for eliminating interference or					
	parasitic voltages or currents}					
19/00353	• • {in bipolar transistor circuits}					
19/00361	• • • {in field effect transistor circuits}					
19/00369	• • {Modifications for compensating variations of					
	temperature, supply voltage or other physical					
10/00076	parameters}					
19/00376	{in bipolar transistor circuits}					
19/00384 19/00392	 . {in field effect transistor circuits} . {by circuit redundancy (H03K 19/0075 takes 					
19/00392	precedence)}					
19/007	• Fail-safe circuits					
19/0075	• {by using two redundant chains}					
19/01	• Modifications for accelerating switching					
19/013	in bipolar transistor circuits					
19/0133	• • • {by bootstrapping, i.e. by positive feed-back}					
19/0136	• • • {by means of a pull-up or down element}					
19/017	in field-effect transistor circuits					
19/01707	• • • {in asynchronous circuits}					
19/01714	• • • • {by bootstrapping, i.e. by positive feed-					
10/01701	back}					
19/01721	{by means of a pull-up or down element}					
19/01728	• • • {in synchronous circuits, i.e. by using clock signals}					
19/01735	• • • {by bootstrapping, i.e. by positive feed-					
17/01/00	back}					
19/01742	• • • {by means of a pull-up or down element}					
19/0175	• Coupling arrangements; Interface arrangements					
	(interface arrangements for digital computers					
	<u>G06F 3/00, G06F 13/00</u>)					
	• • {Interface arrangements}					
19/017518	• • • {using a combination of bipolar and field effect					
10/017507	transistors [BIFET]}					
19/017527	 {with at least one differential stage} {using opto-electronic devices} 					
	 . {Using opto-electronic devices} . {Coupling arrangements; Impedance matching 					
17/01/343	circuits}					
19/017554	• • • {using a combination of bipolar and field effect					
	transistors [BIFET]}					
19/017563	• • • • { with at least one differential stage }					
	• • • {using opto-electronic devices}					

	• {programmable}
19/01759	
19/018	• using bipolar transistors only
19/01806 19/01812	 {Interface arrangements} {with at least one differential stage}
19/01812	{for integrated injection logic (I2L)}
19/01818	
17/01025	circuits}
19/01831	• • • {with at least one differential stage}
19/01837	
19/01843	• • • {with a bidirectional operation}
19/0185	• using field effect transistors only
19/018507	• • • {Interface arrangements}
19/018514	· · · · · · · · · · · · · · · · · · ·
	(<u>H03K 19/018528</u> and <u>H03K 19/018542</u> take precedence)}
19/018521	• • • {of complementary type, e.g. CMOS}
19/018528	• • • • { with at least one differential stage }
	• • • • {of Schottky barrier type [MESFET]}
	•••• { with at least one differential stage }
	• • • • {synchronous, i.e. using clock signals}
19/018557	{Coupling arrangements; Impedance matching
10/010544	circuits}
19/018564	• • • { with at least one differential stage (H03K 19/018578 takes precedence)}
10/018571	• • • {of complementary type, e.g. CMOS}
	• • • • {with at least one differential stage}
	• • • • • • • • • • • • • • • • • • •
	• • {with a bidirectional operation}
19/02	• using specified components
19/02	({ <u>H03K 19/0005</u> - <u>H03K 19/0021</u> },
	({ <u>H03K 19/0005</u> - <u>H03K 19/0021</u> }, <u>H03K 19/003</u> - <u>H03K 19/0175</u> take precedence)
19/04	({ <u>H03K 19/0005</u> - <u>H03K 19/0021</u> }, <u>H03K 19/003</u> - <u>H03K 19/0175</u> take precedence) • using gas-filled tubes
	 (<u>H03K 19/0005 - H03K 19/0021</u>}, <u>H03K 19/003 - H03K 19/0175</u> take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers)
19/04 19/06	({ <u>H03K 19/0005</u> - <u>H03K 19/0021</u> }, <u>H03K 19/003</u> - <u>H03K 19/0175</u> take precedence) • using gas-filled tubes • using vacuum tubes (using diode rectifiers <u>H03K 19/12</u>)
19/04	 ({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers H03K 19/12) using semiconductor devices (H03K 19/173 takes
19/04 19/06	 ({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers H03K 19/12) using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices
19/04 19/06	 ({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers H03K 19/12) using semiconductor devices (H03K 19/173 takes
19/04 19/06 19/08	 ({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers H03K 19/12) using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12)
19/04 19/06 19/08 19/0806	 ({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers H03K 19/12) using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) {using charge transfer devices (DTC, CCD)}
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823	 ({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers H03K 19/12) using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) {using charge transfer devices (DTC, CCD)} {Threshold logic} using bipolar transistors {Multistate logic}
19/04 19/06 19/08 19/0806 19/0813 19/082	 ({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers H03K 19/12) using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) {using charge transfer devices (DTC, CCD)} {Threshold logic} using bipolar transistors {Multistate logic} we found of the states being the high
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826	 ({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers H03K 19/12) using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) {using charge transfer devices (DTC, CCD)} {Threshold logic} using bipolar transistors {Multistate logic} {on of the states being the high impedance or floating state}
19/04 19/06 19/08 19/0806 19/0813 19/0823 19/0826 19/084	 ({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers H03K 19/12) using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) {using charge transfer devices (DTC, CCD)} {Threshold logic} using bipolar transistors {Multistate logic} {on of the states being the high impedance or floating state} Diode-transistor logic
19/04 19/06 19/08 19/0806 19/0813 19/0823 19/0823 19/0826 19/084 19/0843	 ({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) using gas-filled tubes using vacuum tubes (using diode rectifiers H03K 19/12) using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) {using charge transfer devices (DTC, CCD)} {Threshold logic} using bipolar transistors {Multistate logic} {on of the states being the high impedance or floating state} Diode-transistor logic {Complementary transistor logic [CTL]}
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/084 19/0843 19/0846	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) {using charge transfer devices (DTC, CCD)} {Threshold logic} using bipolar transistors {Multistate logic} {one of the states being the high impedance or floating state} Diode-transistor logic {Complementary transistor logic [CTL]} {Schottky transistor logic [STL]}</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/0844 19/0843 19/0846 19/086	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} . {Threshold logic} . using bipolar transistors {Multistate logic} {one of the states being the high impedance or floating state} Diode-transistor logic {Complementary transistor logic [CTL]} {Schottky transistor logic [STL]} Emitter coupled logic</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/084 19/0843 19/0846	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} . {Threshold logic} . using bipolar transistors {Multistate logic} {one of the states being the high impedance or floating state} Diode-transistor logic [CTL]} {Schottky transistor logic [STL]} Emitter coupled logic {Emitter function logic [EFL]; Base</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/0844 19/0843 19/0846 19/086	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} {Threshold logic} using bipolar transistors {Multistate logic} {one of the states being the high impedance or floating state} Diode-transistor logic {Schottky transistor logic [CTL]} Emitter coupled logic {Emitter function logic [EFL]; Base coupled logic [BCL]}</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/084 19/0843 19/0846 19/086	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} . {Threshold logic} . using bipolar transistors {Multistate logic} {one of the states being the high impedance or floating state} Diode-transistor logic [CTL]} {Schottky transistor logic [STL]} Emitter coupled logic {Emitter function logic [EFL]; Base</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/084 19/0843 19/0846 19/086	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} . {Threshold logic} . using bipolar transistors {Multistate logic} {one of the states being the high impedance or floating state} Diode-transistor logic {Schottky transistor logic [CTL]} Emitter coupled logic {Emitter function logic [EFL]; Base coupled logic [BCL]} {Stacked emitter coupled logic</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/0843 19/0846 19/0866 19/0866 19/0866 19/088 19/09	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} . {Threshold logic} . using bipolar transistors {Multistate logic} {one of the states being the high impedance or floating state} Diode-transistor logic [CTL]} {Schottky transistor logic [STL]} {Emitter coupled logic {Emitter function logic [EFL]; Base coupled logic [BCL]} Transistor-transistor logic Resistor-transistor logic</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/0843 19/0846 19/0866 19/0866 19/0866 19/0886	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} . {Threshold logic} . using bipolar transistors {Multistate logic} {one of the states being the high impedance or floating state} Diode-transistor logic {Complementary transistor logic [CTL]} {Schottky transistor logic [STL]} {Emitter function logic [EFL]; Base coupled logic [BCL]} {Stacked emitter coupled logic (H03K 19/1738 takes precedence)} Transistor-transistor logic Resistor-transistor logic</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/0843 19/0846 19/0866 19/0866 19/0866 19/088 19/09 19/091	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) {using charge transfer devices (DTC, CCD)} {Threshold logic} using bipolar transistors {Multistate logic} {One of the states being the high impedance or floating state} Diode-transistor logic {Complementary transistor logic [CTL]} {Schottky transistor logic [STL]} {Emitter coupled logic {Stacked emitter coupled logic (H03K 19/173 takes precedence)} Transistor-transistor logic Resistor-transistor logic Integrated injection logic or merged transistor logic</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/0843 19/0846 19/0866 19/0866 19/0866 19/088 19/09	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) {using charge transfer devices (DTC, CCD)} {Threshold logic} using bipolar transistors {Multistate logic} {One of the states being the high impedance or floating state} Diode-transistor logic {Complementary transistor logic [CTL]} {Schottky transistor logic [STL]} {Stacked emitter coupled logic (H03K 19/1738 takes precedence)} Transistor-transistor logic Transistor-transistor logic {Integrated injection logic or merged transistor logic {Static induction logic [STL] (when</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/0843 19/0846 19/0866 19/0866 19/0866 19/088 19/09 19/091	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} . {Threshold logic} . using bipolar transistors . {Multistate logic} {One of the states being the high impedance or floating state} . Diode-transistor logic [CTL]} {Schottky transistor logic [STL]} {Emitter coupled logic {Emitter function logic [EFL]; Base coupled logic [BCL]} {Stacked emitter coupled logic {Stacked emitter coupled logic {Stacked emitter coupled logic {Stacked emitter coupled logic </pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/084 19/0843 19/0846 19/0863 19/0866 19/0866 19/088 19/09 19/091 19/0912	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} . {Threshold logic} . using bipolar transistors {Multistate logic} so {one of the states being the high impedance or floating state} . Diode-transistor logic [CTL]} {Schottky transistor logic [STL]} {Schottky transistor logic [STL]} {Stacked emitter coupled logic (H03K 19/1738 takes precedence)} Transistor-transistor logic Resistor-transistor logic {Static induction logic [STL] (when the logic function logic [STL] (when the logic function logic [STL] (when the logic function is fullfilled by a fet H03K 19/09414)}</pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/084 19/0843 19/0846 19/086 19/0863 19/0866 19/088 19/09 19/0911 19/0912	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} . {Threshold logic} . using bipolar transistors {Multistate logic} so {one of the states being the high impedance or floating state} . Diode-transistor logic {Complementary transistor logic [CTL]} {Schottky transistor logic [STL]} {Stacked emitter coupled logic (H03K 19/1738 takes precedence)} {Stacked emitter coupled logic {Stacked emitter coupled logic (H03K 19/1738 takes precedence)} {Stacked emitter coupled logic </pre>
19/04 19/06 19/08 19/0806 19/0813 19/082 19/0823 19/0826 19/084 19/0843 19/0846 19/0863 19/0866 19/0866 19/088 19/09 19/091 19/0912	<pre>({H03K 19/0005 - H03K 19/0021}, H03K 19/003 - H03K 19/0175 take precedence) . using gas-filled tubes . using vacuum tubes (using diode rectifiers H03K 19/12) . using semiconductor devices (H03K 19/173 takes precedence; wherein the semiconductor devices are only diode rectifiers H03K 19/12) . {using charge transfer devices (DTC, CCD)} . {Threshold logic} . using bipolar transistors {Multistate logic} {one of the states being the high impedance or floating state} Diode-transistor logic [CTL]} {Schottky transistor logic [CTL]} {Schottky transistor logic [STL]} {Stacked emitter coupled logic (H03K 19/1738 takes precedence)} Transistor-transistor logic {Stacked emitter coupled logic (H03K 19/1738 takes precedence)} Transistor-transistor logic {Static induction logic [STIL] (when the logic function logic [ISL]}</pre>

19/09403	• • • {using junction field-effect transistors
	(<u>H03K 19/096</u> takes precedence)}
19/09407	• • • • {of the same canal type}
19/0941	• • • • {of complementary type}
19/09414	• • • • {with gate injection or static induction
	[STIL] (<u>H03K 19/0912</u> takes precedence)}
19/09418	• • • • {in combination with bipolar transistors
	[BIFET]}
19/09421	• • • {Diode field-effect transistor logic
	(<u>H03K 19/0956</u> , <u>H03K 19/096</u> take
	precedence)}
19/09425	• • • • {Multistate logic (<u>H03K 19/096</u> takes
	precedence)}
19/09429	• • • • {one of the states being the high
	impedance or floating state}
19/09432	• • • • {with coupled sources or source coupled
	logic (<u>H03K 19/096</u> takes precedence)}
19/09436	•••• {Source coupled field-effect logic
	[SCFL]}
19/0944	• • • • using MOSFET {or insulated gate field-
	effect transistors, i.e. IGFET (H03K 19/096
	takes precedence)
19/09441	• • • • {of the same canal type}
19/09443	••••• {using a combination of enhancement
	and depletion transistors}
19/09445	••••• {with active depletion transistors}
19/09446	••••• {using only depletion transistors}
19/09448	• • • • {in combination with bipolar transistors
	[BIMOS]}
19/0948	• • • • using CMOS {or complementary insulated
	gate field-effect transistors}
19/09482	• • • • • {using a combination of enhancement
17/07402	and depletion transistors}
19/09485	• • • • • • {with active depletion transistors}
19/09485	• • • • • • • • • • • • • • • • • • •
19/09487	using Schottky type FET
1)/0)52	{MESFET}({ <u>H03K 19/09421</u> ,
	H03K 19/09432, $H03K 19/096$ take
	precedence)
19/0956	• • • Schottky diode FET logic (<u>H03K 19/096</u>
17/0750	takes precedence)
19/096	• • • • Synchronous circuits, i.e. using clock signals
17/070	{(<u>H03K 19/01728</u> , <u>H03K 19/01855</u> take
	precedence)}
19/0963	• • • • {using transistors of complementary type
	(H03K 19/0966 takes precedence)}
19/0966	• • • • {Self-timed logic}
19/098	• • • • • • • • • • • • • • • • • • •
19/10	using turnel diodes
19/10	using diode rectifiers
19/12	 using order technicis using opto-electronic devices, i.e. light-emitting
19/14	and photoelectric devices electrically- or
	optically-coupled (optical logic elements
	<u>G02F 3/00</u>)
19/16	• using saturable magnetic devices
19/162	
19/162	 using parametrons using ferro-resonant devices
	-
19/166	• • using transfluxors
19/168	• • • using thin-film devices
19/17	• • using twistors
19/173	• using elementary logic circuits as components
19/1731	• • • {Optimisation thereof}

19/1732	• • • • {by limitation or reduction of the pin/
	gate ratio (for data-processing equipment
10/1722	$\frac{G06F 1/22}{(2 - 1)(1 - 1)}$
19/1733	• • {Controllable logic circuits (<u>H03K 19/177</u>
19/1735	takes precedence)}takes precedence)takes pre
19/1735	• • • • {by writing, e.g. uncommitted logic arrays}
19/1730	• • • • {using multiplexers (<u>H03K 19/1738</u> takes
17/1/5/	precedence)}
19/1738	• • • { using cascode switch logic [CSL] or
	cascode emitter coupled logic [CECL]}
19/177	arranged in matrix form
19/17704	•••• the logic functions being realised by the
	interconnection of rows and columns
19/17708	•••• {using an AND matrix followed by an OR
	matrix, i.e. programmable logic arrays}
19/17712	• • • • • {one of the matrices at least being
	reprogrammable }
19/17716	••••• {with synchronous operation, i.e.
	using clock signals, e.g. of I/O or
	coupling register (<u>H03K 19/17712</u> takes precedence)}
19/1772	••••••••••••••••••••••••••••••••••••••
1)/1//2	least one of the logical matrixes}
19/17724	• • • • Structural details of logic blocks
19/17728	••••• Reconfigurable logic blocks, e.g. lookup
	tables
19/17732	Macroblocks
19/17736	Structural details of routing resources
19/1774	•••• {for global signals, e.g. clock, reset}
19/17744	•••• {for input/output signals}
19/17748	Structural details of configuration resources
19/17752	for hot reconfiguration
19/17756	•••• for partial configuration or partial
	reconfiguration
19/17758	for speeding up configuration or
	reconfiguration
19/1776	for memories
19/17764	-
19/17768	5
19/17772	
19/1778	Structural details for adapting physical
19/17784	parameters
19/17/84	
19/17/88	
19/17796	
19/18	 using galvano-magnetic devices, e.g. Hall-effect
17,10	devices
19/185	• using dielectric elements with variable dielectric
	constant, e.g. ferro-electric capacitors
19/19	using ferro-resonant devices
19/195	• • using superconductive devices
19/1952	• • • {with electro-magnetic coupling of the control
	current}
19/1954	• • • {with injection of the control current}
19/1956	• • • • {using an inductorless circuit}
19/1958	• • • {Hybrid configuration, i.e. using
	electromagnetic coupling and injection of the
10/20	control current}
19/20	 characterised by logic function, e.g. AND, OR, NOR, NOT circuits (<u>H03K 19/003</u> - <u>H03K 19/01</u>
	take precedence) $(HOSK 19/005 - HOSK 19/01)$

19/21	• EXCLUSIVE-OR circuits, i.e. giving output if input signal exists at only one input;
	COINCIDENCE circuits, i.e. giving output only
19/212	if all input signals are identical••• {using bipolar transistors}
19/212	 . {using field-effect transistors}
19/213	• • • {using Schottky type FET [MESFET]}
19/23	 Majority or minority circuits, i.e. giving output
17/25	having the state of the majority or the minority of the inputs
21/00	Details of pulse counters or frequency dividers
21/02	. Input circuits
21/023	 {comprising pulse shaping or differentiating circuits}
21/026	• • {comprising logic circuits}
21/08	• Output circuits
21/10	• • comprising logic circuits
21/12	• with parallel read-out
21/14	• with series read-out of number stored
21/16	Circuits for carrying over pulses between successive decades
21/17	• with field effect transistors
21/18	• Circuits for visual indication of the result
21/20 21/38	• using glow discharge lamps
21/38	• Starting, stopping or resetting the counter (counters with a base other than a power of two H03K 23/48, H03K 23/66)
21/40	• Monitoring; Error detection; Preventing or correcting improper counter operation
21/403	• {Arrangements for storing the counting state in case of power supply interruption}
21/406	• • {Synchronisation of counters}
21/406 23/00	Pulse counters comprising counting chains;
	Pulse counters comprising counting chains; Frequency dividers comprising counting chains
23/00	Pulse counters comprising counting chains; Frequency dividers comprising counting chains (<u>H03K 29/00</u> takes precedence)
	Pulse counters comprising counting chains;Frequency dividers comprising counting chains(H03K 29/00 takes precedence). {using elements not covered by groups
23/00	Pulse counters comprising counting chains; Frequency dividers comprising counting chains (<u>H03K 29/00</u> takes precedence)
23/00 23/001	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (<u>H03K 29/00</u> takes precedence) {using elements not covered by groups <u>H03K 23/002</u> and <u>H03K 23/74</u> - <u>H03K 23/84</u>}
23/00 23/001	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (<u>H03K 29/00</u> takes precedence) {using elements not covered by groups <u>H03K 23/002</u> and <u>H03K 23/74</u> - <u>H03K 23/84</u>} {using semiconductor devices (<u>H03K 23/78</u>,
23/00 23/001 23/002	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order,
23/0023/00123/00223/004	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters}
 23/00 23/001 23/002 23/004 23/005 	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code}
23/00 23/001 23/002 23/004 23/005 23/007	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} Gating or clocking signals applied to all stages, i.e.
23/00 23/001 23/002 23/004 23/005 23/007 23/008	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} Gating or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84
23/00 23/001 23/002 23/004 23/005 23/007 23/008	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} Gating or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84 take precedence)} Out-of-phase gating or clocking signals applied to
23/00 23/001 23/002 23/004 23/005 23/007 23/008 23/40 23/42	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} Gating or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84 take precedence)} Out-of-phase gating or clocking signals applied to counter stages
23/00 23/001 23/002 23/004 23/005 23/007 23/008 23/40 23/42 23/425	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} {using or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84 take precedence)} Out-of-phase gating or clocking signals applied to counter stages {using bistables}
23/00 23/001 23/002 23/004 23/005 23/007 23/008 23/40 23/42	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} {using or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84 take precedence)} Out-of-phase gating or clocking signals applied to counter stages {using bistables} using field-effect transistors {(H03K 23/46 and
23/00 23/001 23/002 23/004 23/005 23/007 23/008 23/40 23/42 23/425	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} Gating or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84 take precedence)} Out-of-phase gating or clocking signals applied to counter stages {using bistables} using field-effect transistors {(H03K 23/46 and H03K 23/425 take precedence)} using charge transfer devices, i.e. bucket
23/00 23/001 23/002 23/004 23/005 23/007 23/008 23/40 23/42 23/425 23/44	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} {using biquinary code} Gating or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84 take precedence)} Out-of-phase gating or clocking signals applied to counter stages {using bistables} using field-effect transistors {(H03K 23/46 and H03K 23/425 take precedence)} using charge transfer devices, i.e. bucket brigade or charge coupled devices with a base or radix other than a power of two
23/00 23/001 23/002 23/004 23/005 23/007 23/008 23/40 23/42 23/425 23/44 23/46	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} Gating or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84 take precedence)} Out-of-phase gating or clocking signals applied to counter stages {using bistables} using field-effect transistors {(H03K 23/46 and H03K 23/425 take precedence)} using charge transfer devices, i.e. bucket brigade or charge coupled devices
23/00 23/001 23/002 23/004 23/005 23/007 23/008 23/40 23/42 23/425 23/44 23/46 23/48	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} Gating or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84 take precedence)} Out-of-phase gating or clocking signals applied to counter stages {using bistables} using field-effect transistors {(H03K 23/46 and H03K 23/425 take precedence)} using charge transfer devices, i.e. bucket brigade or charge coupled devices with a base or radix other than a power of two (H03K 23/42 takes precedence) {with a base which is an odd number}
23/00 23/001 23/002 23/004 23/005 23/007 23/008 23/40 23/42 23/425 23/44 23/46 23/48 23/483	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} {using or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84 take precedence)} Out-of-phase gating or clocking signals applied to counter stages {using field-effect transistors {(H03K 23/46 and H03K 23/425 take precedence)} using charge transfer devices, i.e. bucket brigade or charge coupled devices with a base or radix other than a power of two (H03K 23/42 takes precedence) { with a base which is a nod number} { with a base which is a non-integer} using bi-stable regenerative trigger circuits
23/00 23/001 23/002 23/004 23/005 23/007 23/008 23/40 23/42 23/425 23/44 23/425 23/44 23/48 23/483 23/486	 Pulse counters comprising counting chains; Frequency dividers comprising counting chains (H03K 29/00 takes precedence) {using elements not covered by groups H03K 23/002 and H03K 23/74 - H03K 23/84} {using semiconductor devices (H03K 23/78, H03K 23/80, H03K 23/84 take precedence)} {Counters counting in a non-natural counting order, e.g. random counters} {using minimum change code, e.g. Gray Code} {using biquinary code} {using or clocking signals applied to all stages, i.e. synchronous counters {(H03K 23/74 - H03K 23/84 take precedence)} Out-of-phase gating or clocking signals applied to counter stages {using field-effect transistors {(H03K 23/46 and H03K 23/425 take precedence)} using charge transfer devices, i.e. bucket brigade or charge coupled devices with a base or radix other than a power of two (H03K 23/42 takes precedence) {with a base which is a nod number} {with a base which is a non-integer}

23/505	
	• • • • {with a base which is an odd number}
23/507	• • • • {with a base which is a non-integer}
23/52	using field-effect transistors
23/54	Ring counters, i.e. feedback shift register
	counters (<u>H03K 23/52</u> takes precedence)
23/542	• • • • {with crossed-couplings, i.e. Johnson
25/542	counters}
23/544	• • • { with a base which is an odd number }
23/546	• • • { with a base which is a non-integer }
23/548	{Reversible counters}
23/56	Reversible counters (<u>H03K 23/52</u> { and $U02K 22/548$) to be more dense.)
02/59	H03K 23/548} take precedence)
23/58	• Gating or clocking signals not applied
	to all stages, i.e. asynchronous counters
00/500	(H03K 23/74 - H03K 23/84 take precedence)
23/582	• • {with a base or a radix different of a power of
00/504	two}
23/584	• • • {with a base which is an odd number}
23/586	• • • {with a base which is a non-integer}
23/588	• • {Combination of a synchronous and an
	asynchronous counter}
23/60	• • with field-effect transistors
23/62	reversible
23/64	• with a base or radix other than a power of two
	(<u>H03K 23/40</u> - <u>H03K 23/62</u> take precedence)
23/66	• • with a variable counting base, e.g. by presetting
	or by adding or suppressing pulses
23/662	• • • {by adding or suppressing pulses}
23/665	• • • {by presetting}
23/667	• • • {by switching the base during a counting
	cycle}
23/68	• • with a base which is a non-integer
23/70	• • with a base which is an odd number ($H03K 23/66$
	takes precedence)
23/72	• Decade counters (<u>H03K 23/66</u> takes precedence)
23/74	• using relays
23/76	• using magnetic cores or ferro-electric capacitors
23/763	• {using superconductive devices}
23/766	• {using thin-film devices}
23/78	
	using onto-electronic devices
	• using opto-electronic devices
23/80	• using semiconductor devices having only two
23/80	• using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode
23/80 23/82	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes
23/80 23/82 23/825	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes}
23/80 23/82 23/825 23/84	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors
23/80 23/82 23/825	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take
23/80 23/82 23/825 23/84	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors
23/80 23/82 23/825 23/84	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take
23/80 23/82 23/825 23/84 23/86	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence)
23/80 23/82 23/825 23/84 23/86	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and
23/80 23/82 23/825 23/84 23/86 25/00	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers
23/80 23/82 23/825 23/84 23/86 25/00	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis
23/80 23/82 23/825 23/84 23/86 25/00 25/02	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis
23/80 23/82 23/825 23/84 23/86 25/00 25/02	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis using auxiliary pulse generator triggered by the
23/80 23/82 23/825 23/84 23/86 25/00 25/02 25/04 25/12	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis using auxiliary pulse generator triggered by the incoming pulses comprising hysteresis storage
23/80 23/82 23/825 23/84 23/86 25/00 25/02 25/02	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (<u>H03K 23/40</u> - <u>H03K 23/84</u> take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis using auxiliary pulse generator triggered by the incoming pulses comprising hysteresis storage
23/80 23/82 23/825 23/84 23/86 25/00 25/02 25/04 25/12	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis using auxiliary pulse generator triggered by the incoming pulses comprising hysteresis storage Pulse counters in which pulses are continuously circulated in a closed loop; Analogous frequency
23/80 23/82 23/825 23/84 23/86 25/00 25/02 25/04 25/12	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis using auxiliary pulse generator triggered by the incoming pulses comprising hysteresis storage Pulse counters in which pulses are continuously circulated in a closed loop; Analogous frequency dividers
23/80 23/82 23/825 23/84 23/86 25/00 25/02 25/04 25/12	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis using auxiliary pulse generator triggered by the incoming pulses comprising hysteresis storage Pulse counters in which pulses are continuously circulated in a closed loop; Analogous frequency
23/80 23/82 23/825 23/84 23/86 25/00 25/02 25/04 25/12	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis using auxiliary pulse generator triggered by the incoming pulses comprising hysteresis storage Pulse counters in which pulses are continuously circulated in a closed loop; Analogous frequency dividers
23/80 23/82 23/825 23/84 23/86 25/00 25/02 25/04 25/12 25/12 27/00	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis using auxiliary pulse generator triggered by the incoming pulses comprising hysteresis storage Pulse counters in which pulses are continuously circulated in a closed loop; Analogous frequency dividers (feedback shift register counters H03K 23/54)
23/80 23/82 23/825 23/84 23/86 25/00 25/02 25/04 25/12 25/12 27/00	 using semiconductor devices having only two electrodes, e.g. tunnel diode, multi-layer diode using gas-filled tubes {using vacuum tubes} using thyristors or unijunction transistors reversible (H03K 23/40 - H03K 23/84 take precedence) Pulse counters with step-by-step integration and static storage; Analogous frequency dividers comprising charge storage, e.g. capacitor without polarisation hysteresis using auxiliary pulse generator triggered by the incoming pulses comprising hysteresis storage Pulse counters in which pulses are continuously circulated in a closed loop; Analogous frequency dividers (feedback shift register counters H03K 23/54) Pulse counters comprising multi-stable elements,

29/04 29/06	 using multi-cathode gas discharge tubes using beam-type tubes, e.g. magnetrons, cathode-ray tubes 						
99/00	Subject matter not provided for in other groups of this subclass						
2217/00	Indexing scheme related to electronic switching or gating, i.e. not by contact-making or -breaking covered by <u>H03K 17/00</u>						
2217/0009	• AC switches, i.e. delivering AC power to a load						
2217/0018	• Special modifications or use of the back gate voltage of a FET						
2217/0027	• Measuring means of, e.g. currents through or voltages across the switch						
2217/0036	. Means reducing energy consumption						
2217/0045	• Full bridges, determining the direction of the current through the load						
2217/0054	• Gating switches, e.g. pass gates						
2217/0063	• High side switches, i.e. the higher potential [DC] or life wire [AC] being directly connected to the switch and not via the load						
2217/0072	• Low side switches, i.e. the lower potential [DC] or neutral wire [AC] being directly connected to the switch and not via the load						
2217/0081	• Power supply means, e.g. to the switch driver						
2217/009	Resonant driver circuits						
2217/94	• characterised by the way in which the control signal is generated						
2217/94005	activated by voice or sound						
2217/9401	Calibration techniques						
2217/94015	• • Mechanical, e.g. by displacement of a body, a shielding element, or a magnet, in or out of the sensing area						
2217/94021	• • • with human activation, e.g. processes requiring or being triggered by human intervention, user- input of digital word or analog voltage						
2217/94026	• • • Automatic threshold calibration; e.g. threshold automatically adapts to ambient conditions or follows variation of input						
2217/94031	Calibration involving digital processing						
2217/94036	• Multiple detection, i.e. where different switching signals are generated after operation of the user is detected at different time instants at different locations during the actuation movement by two or more sensors of the same or different kinds						
2217/94042	e e, i						
2217/94047							
	• • with evaluation of actuation pattern or sequence, e.g. tapping						
2217/94057	-						
2217/94063	1						
2217/94068	e						
2217/94073	*						
2217/94078							
	• Transmission of parameters among sensors or between sensor and remote station						
	Wireless transmission						
2217/94094	••• Wired transmission, e.g. via bus connection or similar						
	• • using an optical detector						
	characterised by the type of activation						
2217/94104	using a light barrier						

2217/94106	•	•	•	• Passive activation of light sensor, e.g. by ambient light
2217/94108	•	•	•	making use of reflection
2217/94111	•	•	•	having more than one emitter
				having more than one receiver
2217/94114	•	•	•	Optical multi axis
2217/94116	•	•	•	increasing reliability, fail-safe
2217/945	•	•	P	roximity switches
2217/95	•	•	•	using a magnetic detector
2217/952	•	•	•	Detection of ferromagnetic and non-
				magnetic conductive targets
2217/954	•	•	•	Ferromagnetic case
2217/956	•	•	•	• Negative resistance, e.g. LC inductive
				proximity switches
2217/958	•			 involving transponders
2217/96				ouch switches
				using acoustic waves, e.g. ultrasound
2217/96007				• by reflection
				• with propagation, SAW or BAW
2217/96015	•	•	•	Constructional details for touch switches
				(for capacitive touch switches <u>see</u>
2215/0 (010				<u>H03K 2217/9607</u>)
2217/96019				• using conductive paint
2217/96023	•	•	•	• Details of electro-mechanic connections
				between different elements, e.g.: sensing plate and integrated circuit containing
				electronics
2217/96027				Piezoelectric snap spring
2217/96031				Combination of touch switch and LC display
2217/96035				by temperature detection, i.e. body heat
2217/96038				Inductive touch switches
2217/96042		•		with illumination
2217/96042		•		• Key-pad combined with display, back-lit
2217/9605				Detection of leakage or discharge current
221779005	•	•	•	across the touching body to ground
2217/96054				Double function: touch detection combined
				with detection of a movable element
2217/96058				Fail-safe touch switches, where switching takes
				place only after repeated touch
2217/96062	•	•	•	with tactile or haptic feedback
2217/96066	•	•	•	Thumbwheel, potentiometer, scrollbar or slider
				simulation by touch switch
2217/9607	•	•	•	Capacitive touch switches
2217/960705	•	•	•	• Safety of capacitive touch and proximity
				switches, e.g. increasing reliability, fail-safe
2217/96071		•	•	• characterised by the detection principle
2217/960715	•	•	•	• Rc-timing; e.g. measurement of variation
				of charge time or discharge time of the
2217/0/072				sensor
2217/96072	•	•	•	• Phase comparison, i.e. where a phase comparator receives at one input the signal
				directly from the oscillator, at a second
				input the same signal but delayed, with a
				delay depending on a sensing capacitance
2217/960725		•		. Charge-transfer
2217/96073		•		Amplitude comparison
				• characterised by circuit details
2217/96074				-
2217/960745		•	•	-
				with reference capacitance
				-
2217/96075		•	•	• • involving bridge circuit
2217/96075 2217/960755			•	• • involving bridge circuit

2217/96076 with spring electrode
2217/960765 Details of shielding arrangements
2217/96077 comprising an electrode which is floating
2217/960775 Emitter-receiver or "fringe" type detection, i.e. one or more field emitting electrodes and corresponding one or more receiving electrodes
2217/96078 Sensor being a wire or a strip, e.g. used in automobile door handles or bumpers
2217/960785 with illumination
2217/96079 using a single or more light guides
2217/960795 using organic light emitting devices, e.g.
light emitting polymer [OEP] or OLED
2217/965 Switches controlled by moving an element
forming part of the switch
2217/9651 the moving element acting on a force, e.g.
pressure sensitive element
2217/9653 with illumination
2217/9655 using a single or more light guides
2217/9656 using organic light emitting devices, e.g. light emitting polymer [OEP] or OLED
2217/9658 Safety, e.g. fail-safe switching requiring a sequence of movements